

General Description

The AGM403Q combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

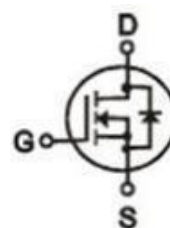
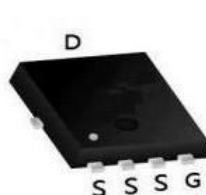
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
40V	2.8mΩ	85A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM403Q	AGM403Q	PDFN5*6	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	85	A
	Drain Current-Continuous(Tc=100°C)	49	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	210	A
PD	Maximum Power Dissipation(Tc=25°C)	70	w
	Maximum Power Dissipation(Tc=100°C)	27	w
EAS	Avalanche energy (Note 3)	100	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	67	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	1.8	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.6	2.5	V
gFS	Forward Transconductance	VDS=5V,ID=20A	--	10	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	2.8	3.8	mΩ
		VGS=4.5V, ID=15A	--	4.0	5.9	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V,VGS=0V, F=1MHZ	--	975	--	pF
Coss	Output Capacitance		--	390	--	pF
Crss	Reverse Transfer Capacitance		--	57	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.5	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=15V, RL=0.75Ω,RGEN=3.3Ω	--	23.2	--	nS
tr	Turn-on Rise Time		--	11.7	--	nS
td(off)	Turn-Off Delay Time		--	38	--	nS
tf	Turn-Off Fall Time		--	14	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=25V, ID=12A	--	24	--	nC
Qgs	Gate-Source Charge		--	6.9	--	nC
Qgd	Gate-Drain Charge		--	2.6	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	85	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.0	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

N-Channel Typical Characteristics

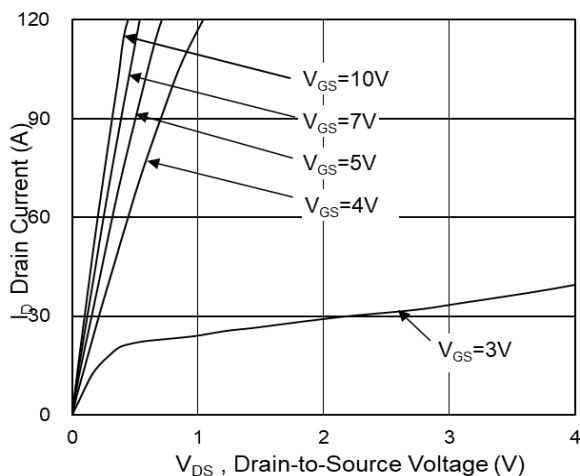


Fig.1 Typical Output Characteristics

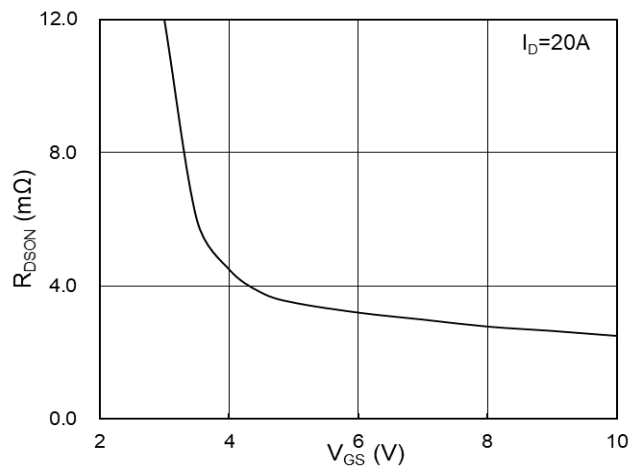


Fig.2 On-Resistance vs G-S Voltage

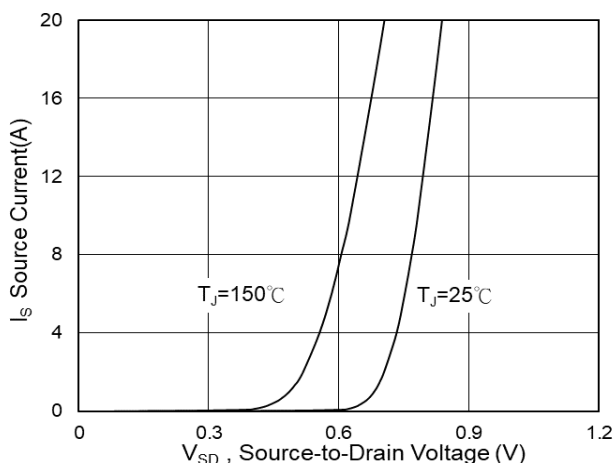


Fig.3 Source Drain Forward Characteristics

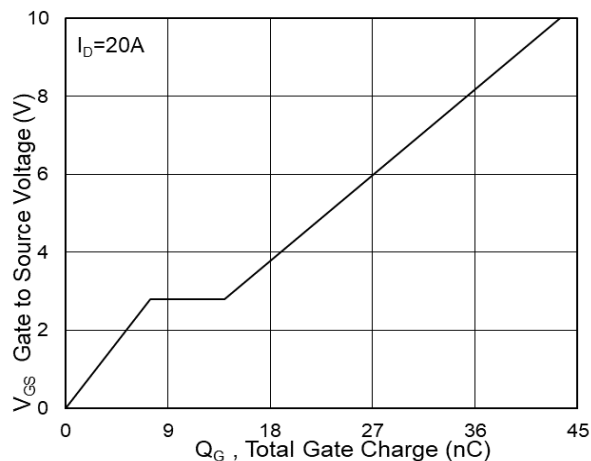


Fig.4 Gate-Charge Characteristics

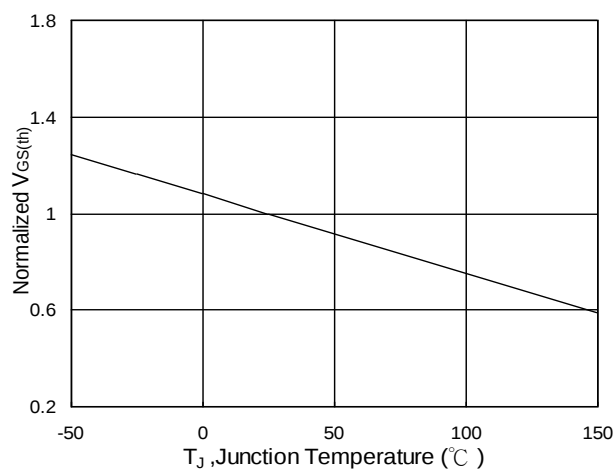


Fig.5 Normalized $V_{GS(th)}$ vs T_J

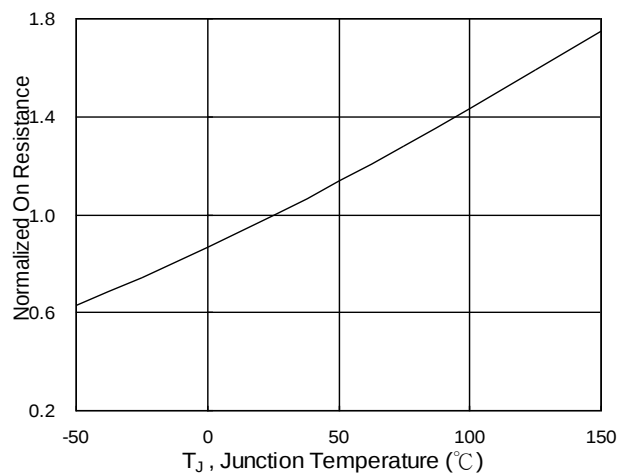


Fig.6 Normalized $R_{DS(on)}$ vs T_J

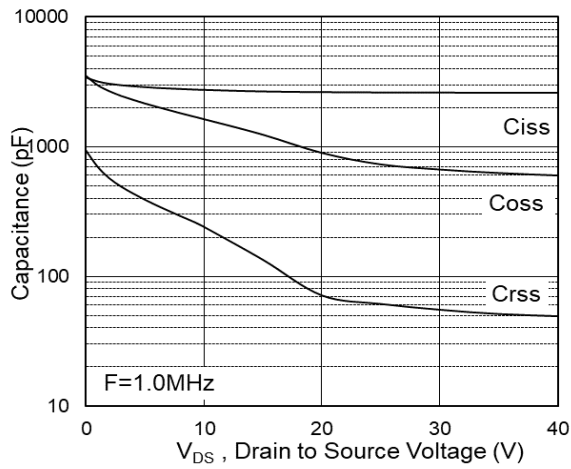


Fig.7 Capacitance

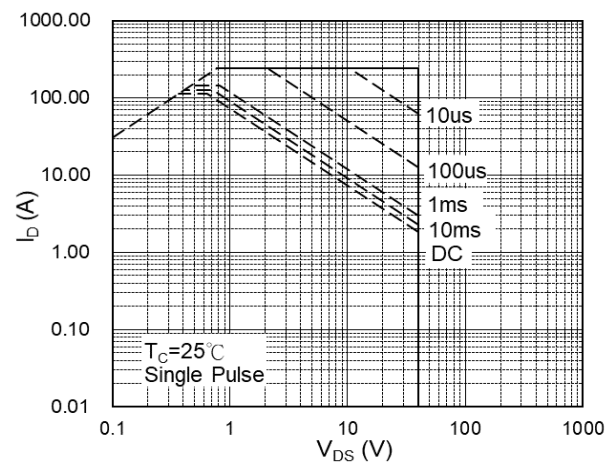


Fig.8 Safe Operating Area

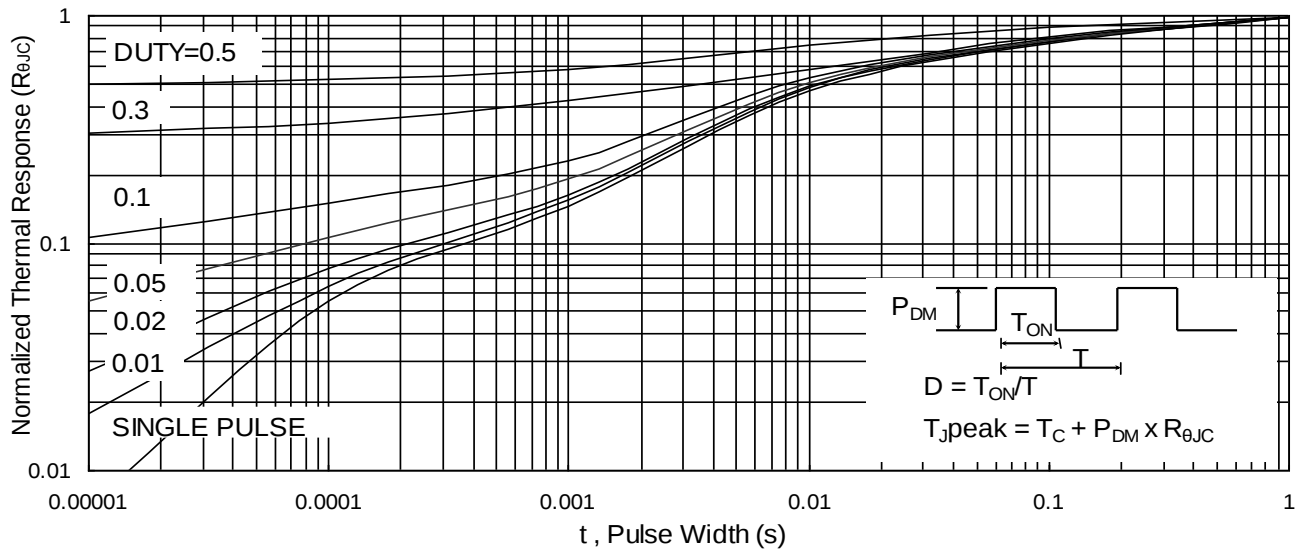


Fig.9 Normalized Maximum Transient Thermal Impedance

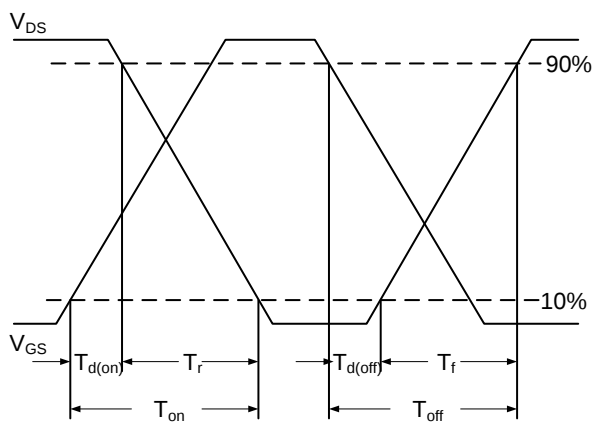


Fig.10 Switching Time Waveform

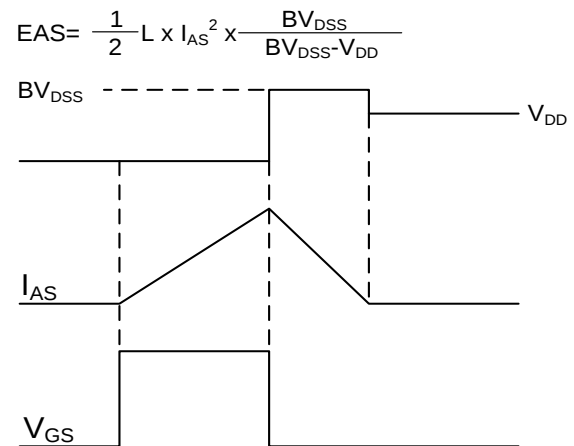
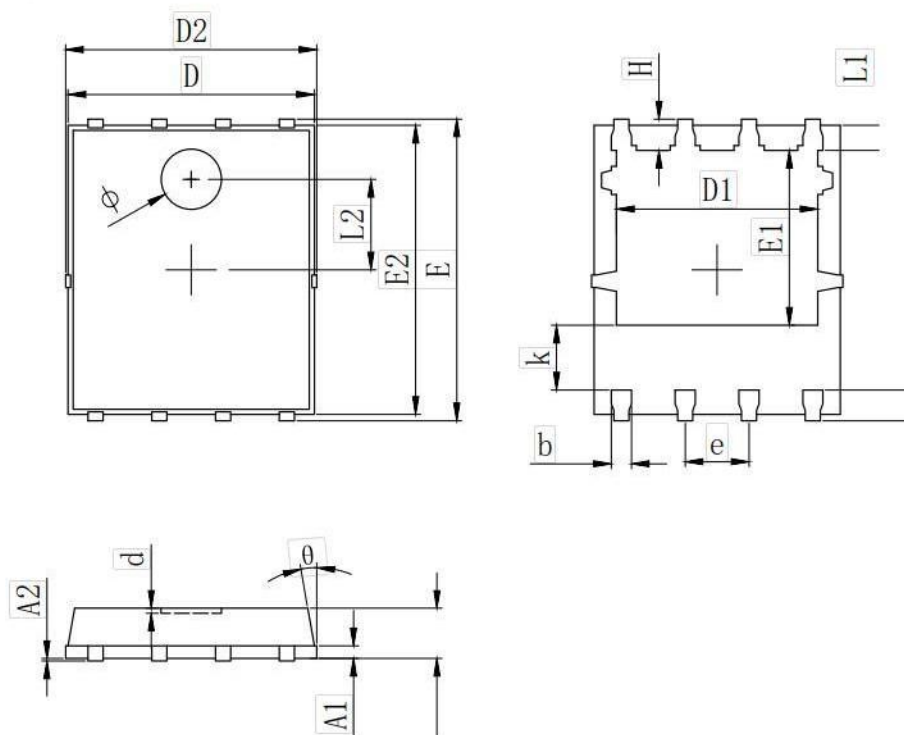


Fig.11 Unclamped Inductive Switching Wave

●Dimensions (DFN5×6)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
○	8°	10°	12°
Ø	1.100	1.200	1.300
d			0.100

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